

**SOT223 NPN SILICON PLANAR HIGH CURRENT  
(HIGH PERFORMANCE) TRANSISTOR**

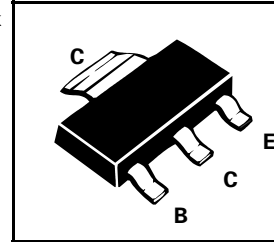
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**FZT857**

**FEATURES**

- \* Up to 3.5 Amps continuous collector current, up to 5 Amp peak
- \*  $V_{CE0} = 300V$
- \* Very low saturation voltage
- \* Excellent  $h_{FE}$  specified up to 3 Amps

PARTMARKING DETAIL - FZT857  
COMPLEMENTARY TYPE - FZT957



**ABSOLUTE MAXIMUM RATINGS.**

PARAMETER	SYMBOL	VALUE	UNIT
Collector-Base Voltage	$V_{CBO}$	350	V
Collector-Emitter Voltage	$V_{CEO}$	300	V
Emitter-Base Voltage	$V_{EBO}$	6	V
Peak Pulse Current	$I_{CM}$	5	A
Continuous Collector Current	$I_C$	3.5	A
Power Dissipation at $T_{amb}=25^{\circ}C$	$P_{tot}$	3	W
Operating and Storage Temperature Range	$T_j; T_{stg}$	-55 to +150	$^{\circ}C$

\*The power which can be dissipated assuming the device is mounted in a typical manner on a P.C.B. with copper equal to 2 inches square.